PCT Applic	ant's Guide - Volume II - National Cha	pter – US Annex US.II, pag
	in Rec'd PCT/PTO	11.111.1997
FORM PTO-1390 U.S. DEPAI (REV 10-05)	RTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTORNEY'S DOCKET NUMBER
DESIGNATED/ELECT	R TO THE UNITED STATES TED OFFICE (DO/EO/US) NG UNDER 35 U.S.C. 371	P-9701 ISK U.S. APPLICATION NO. (If known, 500 37 CFR 5)
INTERNATIONAL APPLICATION NO.	INTERNATIONAL FILING DATE	18/800703
PCT/RU95/000063 TITLE OF INVENTION	April 11, 1995	PRIORITY DATE CLAIMED January 13, 1995
	r Elements with a Plasma Je	t
	Balats, B.; Sinyagin, O.;	Virovets, A.: Shamshurin.
Applicant herewith submits to the United States	Designated/Elected Office (DO/EO/US) the follo	owing items and other information:
	s concerning a filing under 35 U.S.C. 371.	and Antropov,
This is a SECOND or SUBSEQUE!	NT submission of items concerning a filing under	35 U.S.C. 371.
examination until the expiration of the	al examination procedures (35 U.S.C. 371(f)) at a the applicable time limit set in 35 U.S.C. 371(b) ar	d PCT Articles 22 and 39(1).
4. X A proper Demand for International F	reliminary Examination was made by the 19th m	onth from the earliest claimed priority date.
	ication as filed (35 U.S.C. 371(c)(2))	
	(required only if not transmitted by the Intern	national Bureau).
	the International Bureau.	
6. X A translation of the International	oplication was filed in the United States Rece Application into English (35 U.S.C. 371(c)(3	iving Office (RO/US).
	International Application under PCT Article	
	(required only if not transmitted by the Inter	national Bureau).
_	y the International Bureau.	
	wever, the time limit for making such amend	emnts has NOT expired.
d. have not been made and		
	to the claims under PCT Article 19 (35 U.S.C	
- LAI All ball of declaration of the life	ntor(s) (35 U.S.C. 371(c)(4)). (unsign	ed signed originalito
 A translation of the annexes to the (35 U.S.C. 371(c)(5)). 	e International Preliminary Examination Rep	ort under PCT Article 36
Items 11. to 16. below concern documen	it(s) or information included:	
11. An Information Disclosure Statem		
12. X An assignment document for reco	rding. A separate cover sheet in compliance	with 37 CFR 3.28 and 3.31 is included. signment to follow)
 A FIRST preliminary amendment. 		orgament to rorrow)
A SECOND or SUBSEQUENT p	reliminary amendment	
	,	
14. A substitute specification.		
15. A change of power of attorney and	d/or address letter.	
 Other items or information: 		
a) Declaration and Power of	Attorney (unsigned sign	ed original to follow);
b) PCT Notification of the	Recording of a Change (the	name change of assignee):
d) International Bublishi	ional Preliminary Examinat	ion;
Search Report).	on No. WO 96/21943 (together	with International
Mopore,		

r					
U.S. APPLICATION NO. (if	known, see 37 CFR (5)	PCT/RU95/00063		P-9701	
17. The fol	lowing fees are submitte	ed:		CALCULATIONS	PTO USE ONLY
	AL FEE (37 CFR 1.492				
Search Repo	rt has been prepared by	the EPO or JPO	\$880.00		
International	preliminary examination	on fee paid to USPTO (37 CFR 1.4	82)		
		er ereieren erreinin ar a	\$680.00		
No internation but internation	onal preliminary examin onal search fee paid to U	ation fee paid to USPTO (37 CFR JSPTO (37 CFR 1.445(a)(2))	1.482) . \$750.00		
Neither inter international	national preliminary exa search fee (37 CFR 1.4	amination fee (37 CFR 1.482) nor 45(a)(2)) paid to USPTO	\$1010.00		
International and all claim	preliminary examinations of satisfied provisions of	on fee paid to USPTO (37 CFR 1.48 PCT Article 33(2)-(4)	82) . \$94.00		
	ENTER APPR	OPRIATE BASIC FEE AM	IOUNT =	s 1,010.00	
Surcharge of \$130 months from the	0.00 for furnishing the o earliest claimed priority	ath or declaration later than date (37 CFR 1.492(e)).	0 X 30	s 130.00	
CLAIMS	NUMBER FILED	NUMBER EXTRA	RATE		
Total claims	1 -20	- 0	X \$22.00	s	
Independent claims	1 -3		X \$78.00	s	
MULTIPLE DEPE	NDENT CLAIM(S) (if ap		+ \$250.00	S	
		L OF ABOVE CALCULAT		\$ 1,140.00	
Reduction of 1/2 must also by filed	for filing by small entity (Note 37 CFR 1.9, 1.27	r, if applicable. Verified Small Enti 7, 1.28).	ity Statement	S	
		SUBT	OTAL =	S .	
Processing fee of months from the	\$130.00 for furnishing t	the English translation later than date (37 CFR 1.492(f)).	20 30	s	
		TOTAL NATION	AL FEE =	\$ 1,140.00	
		t (37 CFR 1.21(h)). The assignment (37 CFR 3.28, 3.31). \$40.00 per		s 40.00	
		TOTAL FEES ENC	LOSED =	\$ 1,180,00	
	*			Amount to be:	S
				refunded	5
				charged	<u> </u>
a. X A check	in the amount of \$_	1,180.00 to cover the abov	e fees in minclosi n	X will follow	٠.
b. Please c	harge my Deposit Accor cate copy of this sheet is	unt No in the :	amount of \$	to cov	er the above fees.
		thorized to charge any additional fe	sac which may be	required or gradit a	
overpay	ment to Deposit Accoun	it No A duplicat	e copy of this she	eet is enclosed.	,,
NOTE: Where	an appropriate time !	imit under 37 CFR 1.494 or 1.495	5 has not been m	net, a petition to revi	ive (37 CFR
1.137(a) or (b)	must be filed and grai	nted to restore the application to	pending status.	11	
SEND ALL CORRES	PONDENCE TO		/ M	MX DOWN	
Lackenbac P.C.	h Siegel Marzůl	llo Aronson & Greenspa		7 (
	h Siegel Buildi	ing	Myro	n Greenspan	<u> </u>
One Chase				v 05.660	
Scarsdale (914) 723				No. 25,680 Atton number	

Applicant or Patentee: Tokmulin et al.

Serial or Patent No.: 08/860,763

Filed or Issued: July 11, 1997

For: Device for Treating Planar Elements with a Plasma Jet

DECLARATION CLAIMING SMALL ENTITY STATUS

[37 CFR 1.9(f) and 1.27(C)]

SMALL BUSINESS CONCERN

I hereby declare that I am

the owner of the small business concern identified below:

X an official of the small business concern empowered to act on behalf of the concern identified below

NAME OF CONCERN: Az Corporation (Aktsionernoe obshestvo "Nauchno-proizvodstvennaya firma 'Az'"

ADDRESS OF CONCERN: 40 B. Semenovskaya St., 105023 Moscow RUSSIA.

Thereby declare that the above identified small business concern qualifies as a small business concern as defined in 13 CFR .121.3-18, and reproduced in 37 CFR 1.9(d), for purposes of ppying reduced fees under section 41(a) and (b) of Title 35, United \$3 tates Code, in that the number of employees of the concern, including those of its affiliates, does not exceed 500 persons. For purposes of this statement, (1) the number of employees of the business concern is the average over the previous fiscal year of the concern of the persons employed on a full-time, part-time or temporary basis during each of the pay periods of the fiscal year, and (2) concerns are affiliates of each other when cither, directly or indirectly, one concern controls or has the power to control the other, or a third party or parties controls or has the power to control the tother, or a third party or parties controls or has the power to control toth.

I hereby declare that rights under contract or law have been conveyed to and remain with the small business concern identified above with regard to the invention, entitled: described in

- ↑ the specification filed herewith
- X application serial no. 08/860,763, filed July 11, 1997.
- □ patent no. . issued

1 the rights held by the above identified small business concern are not exclusive, each individual, concern or organization Ethaniza rights to the invention is listed below and no rights to the invention are held by any person, other than the inventor, Edwho could not qualify as a small business concern under 37 CFR 1.9(d) or by any concern which would not qualify as a small ground the small property of the small

ANote: Separate verified statements are required from each named person, concern or organization having rights to the invention against the invention against the invention against the status as small entities. (37 CFR 1.27)

t to	FULL NAME: Az Corporation (Zekrytoe Aktsionernoe, Obschestvo "Nauchino-prolzvodstvennaya IIIma Vz. ADDRESS: 40 B.Semenovskaya St., 105023, Moscow, RUSSIA	☐ INDIVIDUAL M SMALL BUSINESS CONCERN D NONPROFIT ORGANIZATION
K . H P . H U .	FULL NAME: ADDRESS:	☐ INDIVIDUAL ☐ SMALL BUSINESS CONCERN. ☐ NONPROFIT ORGANIZATION
a a a a a a	FULL NAME: ADDRESS:	☐ INDIVIDUAL ☐ SMALL BUSINESS CONCERN ☐ NONPROFIT ORGANIZATION

I acknowledge the duty to file, in this application or patent, notification of any change in status resulting in loss of entitlement to small entity status prior to paying, or at the time of paying, the earliest of the issue fee or any maintenance fee due after the date on which status as a small entity is no longer papropriate. G37 CFR 1.2600.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the tike so made are punishable by fine or imprisonment, or both, under Section 1001 of filte 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application, any patent issuing thereon, or amy patent to which this verified declaration is direction.

NAME OF PERSON SIGNING	TITLE
Vyacheslay A. ARKHANGELSKY	Director Genera
SIGNATURE	DATE
	July 31,1997
RESIDENCE ADDRESS	
7-ya Parkovaya St., d.IO, kv.I8, IO5043, Moscow, RUSS	IA

LACKENBACH SIEGEL MARZULIO ARONSON & GREENSPAN, P.C.

SE-B-1

Docket No.: P-9701 ISK

WO 96/21943

88 Rec'd PCT/PTO 1 1 JUN1997 PCT/RU95/00063 Int. Cl.6 H01L 21/302

DEVICE FOR TREATING PLANAR ELEMENTS WITH A PLASMA JET

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to the field of plasma technology and may be used in electronics and electrical engineering when treating planar elements, for example semiconductor wafers, substrates, printed circuit boards, compact disks and other products.

2. Description of the Related Art

There has been known a device for studying a plasma surface interaction, comprising a plasma generator, a power source therefor, a system for the plasma generator displacement, a system for displacing samples, a gas distribution system and a control system (see, Theses of the Reports at the 10th All-Union Conference "Low-Temperature Plasma Generators", Part II, Minsk, ITMS Publishers, Academy of Sciences of Byelorussian Soviet Socialist Republic, 1986, p. 135, Kulik P. P., et al.).

This device has a number of disadvantages.

The absence of a quick-operating loading-unloading system results in high time expenditures and, hence, plasma generator energy consumable to no purpose when replacing plates-samples to be treated.

The lack of the possibility to simultaneously treat several plates-samples one after another decreases the output.

The presence in the device of a plurality of control and measuring means which are inhibitory to the performance of a repeated treatment of samples according to a rigidly prescribed cycle, unambiguously defines this device as being a purely research one.

Taken together, all the above-mentioned results in the fact that the device cannot be used under the series production conditions.

The closest prior art has been described in the International application WO 92/21220, H05H 1/40, 1992, disclosing a device for treating wafers with a plasma jet, comprising a plasma jet generator; gas supplying means; a set of holders for wafers to be treated; said holders being structurally made in the form of a turntable having a drive for effecting angular displacement thereof and facing a generator plasma jet directed downwards; each of the holders being made in the form of a horizontal platform to rotate about the axis passing through the center thereof and being perpendicular to a plane of said platform; said plasma jet and wafer holder having the possibility to be displaced with respect to each other in the direction of at least one axis of coordinates and may be in or out of contact with each other.

Main drawbacks associated with this device reside in an underproductivity limited by a large volume of manual operations when loading-unloading the wafers to be treated. In so doing, the wafers treated are inferior in quality due to a

possible damage of their surface when contact-attaching in the holder.

Moreover, the direction of a plasma jet from top to bottom necessitates the measure-taking on the provision of cooling the plasma generator from overheating with upward-coming hot gases formed during operation of the plasma generator.

SUMMARY OF THE INVENTION

According to the present invention, there is provided a device for treating wafers with a plasma jet, comprising a plasma jet generator, gas supplying means, a set of holders for wafers to be treated. The holders have a drive for effecting angular displacement thereof and face a generator plasma jet, each of the holders being made in the form of a horizontal platform to rotate about the axis passing through geometric center thereof and being perpendicular to a plane of said platform. Said plasma jet and wafer holder have the possibility to be displaced with respect to each other in the direction of at least one axis of coordinates and they may be in or out of contact with each other. The device further comprises a manipulator, storage devices for the wafers to be treated, and a closed chamber having a gas exchange system with the wafer holders and a plasma jet generator located inside said chamber such that a plasma jet is directed from bottom upwards in respect of a plane of locating horizontal platforms of said wafer holders. The closed chamber is provided with a window in which a movable shutter is installed. The manipulator is located to contact with said storage devices directly and with said wafer holder indirectly, through the chamber window. Each of the wafer holders is provided with a limiter at the edges and has its horizontal platform provided with at least three vortex chambers and three tangential channels being perpendicular to a plane of said horizontal platform, wherein each of said vortex chambers is provided with an open portion located on a level end surface of the wafer holder, coupled through a tangential channel to said gas supplying means and located such that vortex flows formed afford holding of the platform near the holder and cooling of its individual areas to equalize, over the wafer surface, an amount of energy used for treating thereof. Said limiters on the wafer holder platforms are fabricated as the rods mounted at an angle $\alpha > 90^\circ$ to the plane of said horizontal platform of the wafer holder. In so doing, their length, I, is chosen such that

 $21 \sin (\alpha > 90^{\circ}) > \Delta$

where Δ denotes a maximum deviation from axisymmetric arrangement of the treated wafers in said storage devices.

The technical result of using the proposed device is attained by the following features in accordance with the present invention.

Provision of the device with a common rotary drive for the holders, said drive being mounted inside the closed chamber and having its actuating mechanism connected to each of the holders, greatly enhances output of the device.

Introduction of a manipulator with storage devices for the wafers to be treated makes it possible to further enhance the treatment capacity at the expense of reducing a time needed for loading-unloading the wafers.

The use of a wafer holder having at least three vortex chambers and three tangential channels with the axes of said vortex chambers perpendicular to the horizontal platform of the holder, where each of said vortex chambers being coupled to the tangential channel connected to gas supplying means, allows achievement of a stable holding of the wafer to be treated in the vicinity of the holder with a gas gap without touching the wafer and the holder which, in turn, enables to upgrade the treatment quality due to the absence of the touch traces (scratches).

Arrangement of each of the vortex chambers in the holder such that vortex flows formed by said vortex chambers enable the fulfillment, at each site of the wafer surface, of the condition for $Q_0 = Q_1 + Q_2$

where:

 Q_0 = const - an amount of energy for heating the wafer in the given site;

Q₁ - an amount of energy received by the given site of the wafer surface with due regard to thermal transparency thereof:

 ${\sf Q}_2$ - an amount of energy available at the expense of interaction with a material of the wafer surface in the given site,

makes it possible to produce more uniform, and hence, high-quality treatment of the wafer.

This is conditioned by the fact that each vortex chamber, when creating a gas vortex, makes it possible not only to hold

the wafer near the holder but also to cool individual areas of the wafer to be treated. Since in the process for treatment, different sites on the surface of the wafer to be treated are under different thermal conditions, then proceeding from an energy balance, vortex flows enable establishment of the conditions to equalize Q_0 at all sites of the wafer.

The use of limiters on the holders in the form of the rods mounted at an angle $\alpha > 90^{\circ}$ to the horizontal platform of the holder, with their length, I, being chosen such that

$$21 \sin (\alpha > 90^{\circ}) > \Delta$$

where Δ denotes a maximum deviation from axisymmetric arrangement of the wafers in said storage devices, offers a required accuracy when loading-unloading the wafers, without using additional centering means.

BRIEF DESCRIPTION OF THE DRAWINGS

Other objects and advantages of the invention will be apparent from the following description when taken in connection with the accompanying drawings, in which:

FIG. 1 is a view showing a device for treating wafers with a plasma iet;

FIG. 2 is a view A of FIG. 1;

FIG. 3 is a functional diagram of an actuating mechanism of a common rotary drive for holders;

FIG. 4 is a view showing a wafer holder;

FIG. 5 is a sectional view A-A of FIG. 4.

BEST MODE TO CARRY OUT THE INVENTION

Referring to FIGS. 1, 2, there is illustrated a device for treating wafers with a plasma jet, comprising a closed chamber 1; a gas exchange system 2; a power supply unit 3; gas supplying means 4, a control system 5. The closed chamber 1 is provided with a window 6 in which a movable shutter 7 with a drive 8 is installed. Inside the closed chamber 1, on a base 9, there are located a generator 10 of a plasma jet 11, an angular displacement drive 12 with its upright shaft 13 coupled to holders 14. The generator 10 of the plasma jet 11 facing the holders 14 is mounted on the base 9 on a support 15 adjustable for height such that the axis of the plasma jet 11 and respective axes of each of the holders 14 are equidistant from the axis of the upright shaft 13 of the angular displacement drive 12. Referring to FIG. 4, the holders 14 are made in the form of horizontal platforms 16 with limiters 17. Said limiters 17 are fabricated as the rods, for example cylindrical rods. With reference to FIG. 3, it is seen that the horizontal platforms 16 are set in rotation about their axes by a drive 18, for example by means of an actuating mechanism 19 through a step-by-step interaction of its gears 20, 21, 22 and pulleys 23, 24. It is illustrated in FIGS. 4 and 5 that the horizontal platforms 16 are provided with vortex chambers 25 each having an open portion located on a level end surface of the holder 14 and coupling to a tangential channel 26 connected to said gas supplying means 4. It is shown in FIG. 1 that outside the closed chamber 1, on the base 9, a manipulator 27 and storage devices 28 for wafers 29 are mounted

8

INDUSTRIAL APPLICABILITY

The device operates as follows.

In the initial state, one of the storage devices 28 is provided with wafers 29, while the other is free from the wafers.

A manipulator 27 serves to grip a bottom wafer 29 in the storage device 28 and to transport it through a window 6 (with a shutter 7 opened by a drive 8) inwards a closed chamber 1.

At that moment, a first of the holders 14 is under loading. The manipulator 27 conveys the wafer 29 in a position below a horizontal platform 16 of the first holder 14.

By switching gas supplying means 4 in vortex chambers 25, 26 of the holder 14, gas vortex flows are generated to provide for the holding of the wafer 29 at a distance of about 0.5 - 1.0 mm from a level end surface of the platform 16 of the holder 14. At that moment, the manipulator 14 releases the wafer 29. The wafer has been loaded. Thereupon, the next wafer is loaded.

In an embodiment as illustrated here, a device for treating wafers with a plasma jet is provided with five wafer holders located at an angle of 72° to one another in the horizontal plane. Feeding the next holder in the loading zone is performed with an angular displacement drive 12 for the holder 14.

On loading of all the holders, the manipulator 27 is withdrawn from the closed chamber 1 while closing the shutter 7 with the drive 8. A required gas is supplied to the chamber.

By means of a support 15, a generator 10 of a plasma jet 11 is mounted, with respect to the surface of the wafer 29 to be treated, at a height suitable for a manufacturing process.

On switching the drive 18, the holders 14 start rotation, together with the wafers 29, about their axes. In so doing, a control system 5 is used to specify dynamics of the wafer movement. The generator 10 of the plasma jet 11 and the angular displacement drive 12 are switched and the treatment is carried out.

Following a prescribed number of contacts of the wafer 29 with the plasma jet 11 of the generator 10, the drive 12 is brought to a stop, under the predetermined program from the control system 5, such that none of the wafers 29 in the holders 14 falls within the zone of action of the generator plasma jet.

Then, the drive 18 and the generator 10 are turned off.

Hereinafter, the cycle is repeated using the next batch of wafers.

Various modifications may be made without departing from the spirit or scope of the general inventive concept as defined by the appended claims.

WHAT IS CLAIMED IS:

A device for treating wafers with a plasma jet, comprising a plasma jet generator; gas supplying means; a set of holders for wafers to be treated; said holders having a drive for effecting angular displacement thereof and facing a generator plasma jet; each of the holders being made in the form of a horizontal platform to rotate about the axis passing through geometric center thereof and being perpendicular to a plane of said platform; said plasma jet and wafer holder having the possibility to be displaced with respect to each other in the direction of at least one axis of coordinates and may be in or out of contact with each other, characterized in that it additionally comprises a manipulator; storage devices for the wafers to be treated; and a closed chamber having a gas exchange system with the wafer holders and a plasma jet generator located inside said chamber such that a plasma jet is directed from bottom upwards in respect of a plane of locating horizontal platforms of said wafer holders; said closed chamber is provided with a window in which a movable shutter is mounted; said manipulator is located to contact with said storage devices directly and with said wafer holder indirectly. through the chamber window; each of the wafer holders is provided with a limiter at the edges and has its horizontal platform provided with at least three vortex chambers and three tangential channels being perpendicular to a plane of said horizontal platform: each of said vortex chambers is provided

with an open portion located on a level end surface of the wafer holder, coupled through a tangential channel to said gas supplying means and located such that vortex flows formed afford holding of the platform near the holder and cooling of its individual areas to equalize, over the wafer surface, an amount of energy used for treating thereof; said limiters on the wafer holder platforms are fabricated as the rods mounted at an angle $\alpha > 90^{\circ}$ to the plane of said horizontal platform of the wafer holder, and their length. It is chosen such that

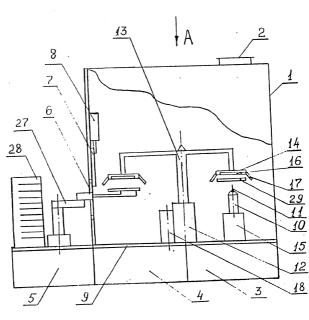
$$21 \sin (\alpha > 90^{\circ}) > \Delta$$

where Δ denotes a maximum deviation from axisymmetric arrangement of the treated wafers in said storage devices.

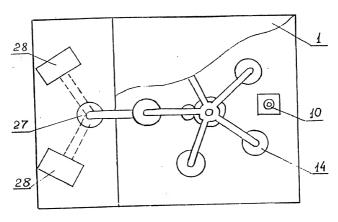
ABSTRACT

Used in the technical field of plasma treatment of planar elements such as plates, sheets and wafers in electronics and electrical engineering, the invention in essence is a device for treating wafers with a plasma jet. The device comprises the following elements mounted in a closed chamber (1): a drive (12) which effects angular displacement of the holders (14) which are provided with a common rotary drive (18); a plasma jet generator (10); and, mounted outside the closed chamber (1), a manipulator (27) and storage devices (28) for the wafers (29). The wafer (29) to be treated is picked up by the manipulator (27) from the storage device (28) and placed in the holder (14) which together with the wafer (29) passes over the plasma jet generator (10) used for the treatment. The cycle may be repeated a predetermined number of times.

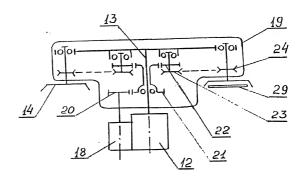
1 Claim, 5 Drawing Figures



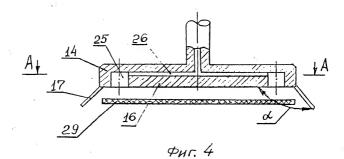
Фиг. 1

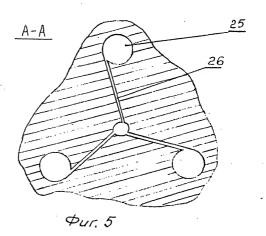


Pur. 2.



Фиг.3





the specification of which

DECLARATION FOR PATENT APPLICATION

As a below-named inventor, I hereby declare that:

(check one)

My residence, post office address and citizenship are as stated below next to my name,

is attached hereto. X was filed on July 11, 1997

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

Attorney's Docket No.: P-9701 ISK

DEVICE FOR TREATING PLANAR ELEMENTS WITH A PLASMA JET

		Application	011 SCITAL NO.: <u>06/600,763</u>	
		and was a	amended on	
			(if applicable)	
	I hereby state that I have claims, as amended by any		and the contents of the above-ident to above.	ified specification, including the
	I acknowledge the duty to Federal Regulations, §1.5		which is material to patentability	as defined in Title 37, Code o
and the second	patent or inventor's certif	ficate listed below and ng a filing date before	Fitle 35, United States Code, \$119 of d have also identified below any for that of the application on which programs of the application on which programs of the application on which programs of the application of the appli	reign application for patent o
	Appln. No.	Country	Date Filed	Priority Claimed
	95100180	Russia	January 13, 1995	X YES NO
	PCT/RU95/00063	PCT	April 11, 1995	X YES NO
				☐ YES ☐ NO
				☐ YES ☐ NO

I hereby claim the benefit under Title 35, United States Code, §120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code §112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, \$1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

Filing Date	Status: Patented, Pending, Abandoned
	☐ Patented ☐ Pending ☐ Abandoned
	☐ Patented ☐ Pending ☐ Abandoned
	Patented Pending Abandoned

POWER OF ATTORNEY

I hereby appoint the following attorney(s) and/or agent(s) to prosecute the application entitled <u>DEVICE FOR TREATING PLANAR ELEMENTS WITH A PLASMA JET</u> and to transact all business in the Patent and Trademark Office connected therewith:

HENRY A. MARZULLO, JR., Reg. No. 20,910; HOWARD N. ARONSON, Reg. No. 27,302; and MYRON GREENSPAN, Reg. No. 25,680.

Address all telephone calls to Myron Greenspan, at telephone number (914) 723-4300, or to the attorney executing the last document.

Address all correspondence to LACKENBACH SIEGEL MARZULLO ARONSON & GREENSPAN, P.C. at Penthouse Suite, One Chase Road, Scarsdale, New York 10583 U.S.A.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full Name of First or Sole Inventor Iskander M. Tokmulin	Citizenship Russian	
RESIDENCE Address Street c/o IPEC Precision, 3 Berkshire Boulevard	POST OFFICE Address Street (same as residence)	
City (Zip) Bethel	City (Zip)	
State or Country Connecticut 06801	State or Country	
Date	Signature	
Full Name of Second Joint Inventor Igor P. Bagriy	Citizenship Russian	
RESIDENCE Address Street c/o IPEC Precision, 3 Berkshire Boulevard	POST OFFICE Address Street (same as residence)	
City (Zip) Bethel	City (Zip)	
State or Country Connecticut 06801	State or Country	
Date	Signature	
Full Name of Third Joint Inventor Boris M. Balats	Citizenship Russian	
RESIDENCE Address - Street Ukhtomskaya St., d. 13, kv. 43	POST OFFICE Address Street (same as residence)	
City (Zip) 111020 Moscow	City (Zip)	
State or Country RUSSIA	State or Country	
Date 41, 08, 97	Signature (MILA)	

Power of Attorney, for Tokmulin et al., "Device for Treating Planar Elements with a Plasma Jet Page 2.

Full Name of Fourth Joint Inventor Oleg V. Sinyagin	Citizenship Russian
RESIDENCE Address Street	POST OFFICE Address Street (same as residence)
City (Zip)	City (Zip)
State or Country	State or Country
Date	Signature
Full Name of Fifth Joint Inventor Alexei B. Virovets	Citizenship Russian
RESIDENCE Address Street 144 Painter Road	POST OFFICE Address Street (same as residence)
City (Zip) Southbury	City (Zip)
State or Country Connecticut 06488	State or Country
Date	Signature
Full Name of Sixth Joint Inventor Vyacheslav G. Shamshurin	Citizenship Russian
RESIDENCE Address Street Krasnopolyanskaya St., d. 35, kv. 124	POST OFFICE Address Street (same as residence)
City (Zip) 141730 Moskovskaya oblast', Lobnya	City (Zip)
State or Country RUSSIA	State or Country
Date U.O.S.97	Signature
Full Name of Seventh Joint Inventor Aleksandr M. Antropov	Citizenship Russian
RESIDENCE Address Street	POST OFFICE Address Street (same as residence)
City (Zip)	City (Zip)
State or Country	State or Country
Date	Signature

UNITED STATES -- PATENT DECLARATION FOR PATENT APPLICATION

As a below-named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

Attorney's Docket No.: P-9701 ISK

the specification of which	n heck one)	☐ is attached he	awatta.	
(6)	песк опе)	☐ IS attached in	arcio.	
		X was filed on _ Application Seri and was amende	July 11, 1997, al No.: 08/860,763 ed on	as,
I hereby state that I have claims, as amended by an		ınd understand the	contents of the above-ide	entified specification, including
		mornion mion	manage to parental	ity as defined in Title 37, Code
Federal Regulations, §1.5 I hereby claim foreign pr patent or inventor's cert	riority bene ificate liste- ing a filing	d below and have	, United States Code, §11 also identified below any f the application on which	19 of any foreign application(s) y foreign application for patent n priority is claimed:
Federal Regulations, §1.5 I hereby claim foreign prepatent or inventor's certinventor's certificate having prior Foreign Application	riority bene ificate liste- ing a filing	d below and have date before that o	also identified below any	y foreign application for patent
Federal Regulations, §1.5 I hereby claim foreign proportion or inventor's certificate having prior Foreign Application	riority bene ificate liste ing a filing n(s):	d below and have date before that o	also identified below any f the application on which	y foreign application for patent n priority is claimed:
Federal Regulations, §1.: I hereby claim foreign pripatent or inventor's certinventor's certinventor's certinventor's certinventor's certificate having the prior Foreign Application Appln. No.	ciority bene ificate liste ing a filing n(s):	d below and have date before that o	also identified below any f the application on which	y foreign application for patent a priority is claimed: Priority Claimed
Federal Regulations, §1.5 I hereby claim foreign propatent or inventor's certineentor's certificate having prior Foreign Application Appln. No. 95100180	riority bene ificate liste ing a filing n(s): Count Russia	d below and have date before that o	also identified below any f the application on which Date Filed January 13, 1995	y foreign application for patent n priority is claimed: Priority Claimed X YES NO

below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code §112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, §1.56(a) which became available between the filing date of the prior application and the national or PCT international filing date of this application:

Appln. Serial No.	Filing Date	Status: Patented, Pending, Abandoned
		☐ Patented ☐ Pending ☐ Abandoned
		☐ Patented ☐ Pending ☐ Abandoned
		☐ Patented ☐ Pending ☐ Abandoned

POWER OF ATTORNEY

I hereby appoint the following attorney(s) and/or agent(s) to prosecute the application entitled <u>DEVICE FOR TREATING PLANAR ELEMENTS WITH A PLASMA JET</u> and to transact all business in the Patent and Trademark Office connected therewith:

HENRY A. MARZULLO, JR., Reg. No. 20,910; HOWARD N. ARONSON, Reg. No. 27,302; and MYRON GREENSPAN, Reg. No. 25,680.

Address all telephone calls to Myron Greenspan, at telephone number (914) 723-4300, or to the attorney executing the last document.

Address all correspondence to LACKENBACH SIEGEL MARZULLO ARONSON & GREENSPAN, P.C.

at Penthouse Suite, One Chase Road, Searsdale, New York 19583 U.S.A.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

ull Name of First or Sole Inventor kander M. Tokmulin	Citizenship Russian
RESIDENCE Address - Street c/o IPEC Precision, 3 Berkshire Boulevard	POST OFFICE Address Street (same as residence)
City (Zip) Bethel	City (Zip)
State or Country Connecticut 06801	State or Country
Date 09/02/57	Signature all I. TOKMOULINE
Full Name of Second Joint Inventor	Citizenship Russian
RESIDENCE Address Street c/o IPEC Precision, 3 Berkshire-Boulevard	POST OFFICE Address - Street (same as residence)
City (Zip) Bethel	City (Zip)
State or Country Connecticut 06801	State or Country
Date 09/03/97	Signature S
Full Name of Third Joint Inventor Boris M. Balats	Citizenship Russian
RESIDENCE Address Street Ukhtomskaya St., d. 13, kv. 43	POST OFFICE Address Street (same as residence)
City (Zip) 111020 Moscow	City (Zip)
State or Country RUSSIA	State or Country
Date	Signature

X Additional inventors are being named on separately numbered sheets attached hereto.

Power of Attorney, for Tokmulin et al., "Device for Treating Planar Elements with a Plasma Jet"

rage 2	
Full Name of Fourth Joint Inventor Oleg V-Sinyagin	Citizenship Russian
RESIDENCE Address Street	POST OFFICE Address Street (same as residence)
City (Zip)	City (Zip)
State or Country	State or Country
Date	Signature
Full Name of Fifth Joint Inventor Alexei B. Virovets	Citizenship Russian
RESIDENCE Address Street 144 Painter Road	POST OFFICE Address Street (same as residence)
City (Zip) Southbury	City (Zip)
State or Country Connecticut 06488	State or Country
Date 09/02/97	Signature Meer
Full Name of Sixth Joint Inventor Vyacheslay G. Shamshurin	Citizenship Russian
Garage Control of the	Hussian
RESIDENCE Address Street Krasnopolyanskaya St., d. 35, kv. 124	POST OFFICE Address Street (same as residence)
RESIDENCE Address Street	POST OFFICE Address Street
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast', Lobnya State or Country RUSSIA	POST OFFICE Address Street (same as residence)
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast, Lobnya State or Country RUSSIA Date	POST OFFICE Address Street (same as residence) City (Zip)
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast', Lobnya State or Country RUSSIA	POST OFFICE Address - Street (same as residence) City (Zip) State or Country
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast', Lobnya State or Country RUSSIA Date	POST OFFICE Address - Street (same as residence) City (Zip) State or Country Signature
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast', Lobnya State or Country RUSSIA Date Full Name of Seventh Joint Inventor Aleksandr M. Antropov	POST OFFICE Address - Street (same as residence) City (Zip) State or Country Signature Citizenship Russian POST OFFICE Address - Street
RESIDENCE Address - Street Krasnopolyanskaya St., d. 35, kv. 124 City (Zip) 141730 Moskovskaya oblast', Lobnya State or Country RUSSIA Date Full Name of Seventh Joint Inventor Aleksandr M. Antropov RESIDENCE Address - Street	POST OFFICE Address - Street (same as residence) City (Zip) State or Country Signature Citizenship Russian POST OFFICE Address - Street (same as residence)

IN THE UNITED STATES PAINT AND TRANSPARSE OFFICE

Applicates): TORMULIN STAL.

ALIGNE: AZ CORPORATION

THE DEVICE FOR TREATING PLANAR ELEMENTS WITH BERINDS FRENCH THEY !! 1494

Dominic

Group Art Unit:

DodstNo.: P . 9701 ISK

Assistant commissioner for patents Washington D. C. 20231

POWER TO INSPECT AND MAKE COPIES

Dear Sire

This constructed on authorizes and grants Terry Kalmatiky or her associate of TK, Associates, 2001 Jefferson Davis Highway, Suin 200, Arlington, Virginia 22202, the power to impost the subject patent application and to make copics of any dominates consultant therein.

Any questions consecuting this Power to impost absorbed to discussed to the underentiated attempt for applicant(s) at the another below.

No. 914-723-4300 Fer Ro. 914-728-4301